

# 1N4448

## FEATURES :

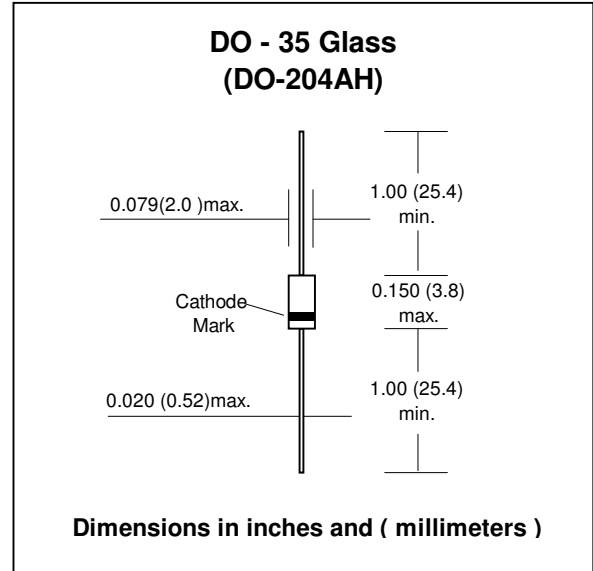
- High switching speed: max. 4 ns
- Reverse voltage: max. 75V
- Peak reverse voltage: max. 100 V
- Pb / RoHS Free

## MECHANICAL DATA :

**Case:** DO-35 Glass Case

**Weight:** approx. 0.13g

## HIGH SPEED SWITCHING DIODE



## Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	100	V
Maximum Reverse Voltage	$V_R$	75	V
Maximum Continuous Forward Current	$I_F$	200	mA
Maximum Average Forward Current <sup>(1)</sup> Half Wave Rectification with Resistive Load , $f \geq 50$ Hz	$I_{F(AV)}$	150	mA
Maximum Surge Forward Current at $t < 1$ s , $T_j = 25^\circ\text{C}$	$I_{FSM}$	0.5	A
Maximum Power Dissipation	$P_D$	500	mW
Maximum Junction Temperature	$T_J$	175	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-65 to + 175	$^\circ\text{C}$

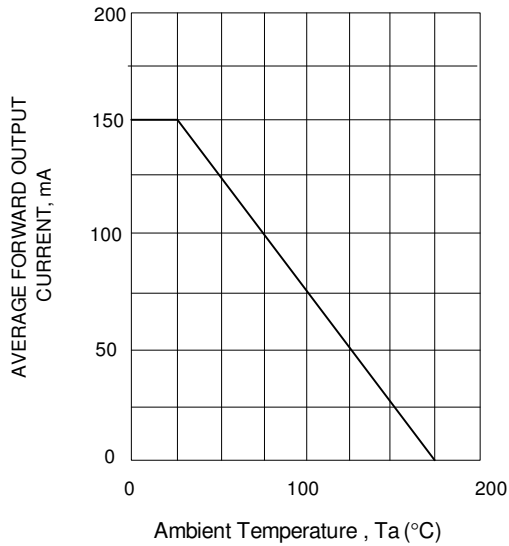
**Note :** (1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

## Electrical Characteristics ( $T_j = 25^\circ\text{C}$ unless otherwise noted)

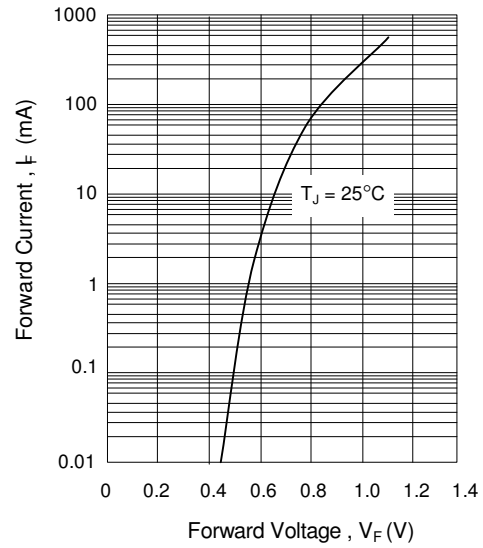
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Current	$I_R$	$V_R = 20$ V	-	-	25	nA
		$V_R = 20$ V , $T_j = 150$ $^\circ\text{C}$	-	-	50	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 10$ mA	-	-	1.0	V
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100$ $\mu\text{A}$ (pulsed)	100	-	-	V
Diode Capacitance	Cd	$f = 1$ MHz ; $V_R = 0$	-	-	4.0	pF
Reverse Recovery Time	$T_{rr}$	$I_F = 10$ mA to $I_R = 1$ mA $V_R = 6$ V , $R_L = 100$ $\Omega$	-	-	4.0	ns

### RATING AND CHARACTERISTIC CURVES ( 1N4448 )

**FIG. 1 MAXIMUM FORWARD CURRENT VERSUS AMBIENT TEMPERATURE**



**FIG. 2 TYPICAL FORWARD VOLTAGE**



**FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE**

